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J Robertson, T Ytterdal, WCB Peatman, RS Tsai, ER ... - IEEE TRANSACTIONS ON ELECTRON DEVICES, 1997 - [ieeexplore.ieee.org](#)

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RS Tsai, Y Chen - US Patent 6,711,723, 2004 - [Google Patents](#)

... (75) Inventors: **Roger S. Tsai**, Terrance, CA (US); Yaochung Chen, Rancho Palos Verdes, CA (US) (73) Assignee: Northrop Grumman Corporation, Los Angeles, CA (US) ...

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(75) Inventors: Ronald W. Grundbacher, Hermosa Beach, CA (US); Richard Lai, Redondo Beach, CA (US); Mark Kintis, Manhattan Beach, CA (US); Michael E. ...

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... (54) EMBEDDING PARASITIC MODEL FOR PI- FET LAYOUTS (75) Inventor: **Roger S. Tsai**,

Terrance, CA (US) (73) Assignee: TRW Inc., Redondo Beach, CA (US) ...

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(75) Inventors: Ronald W. Grundbacher, Hermosa Beach; Richard Lai, Redondo Beach; **Roger S. Tsai**, Torrance; Michael E. Barsky, Sherman Oaks, all of CA ...

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MODELS (75) Inventor: **Roger S. Tsai**, Terrance, CA (US) ...

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